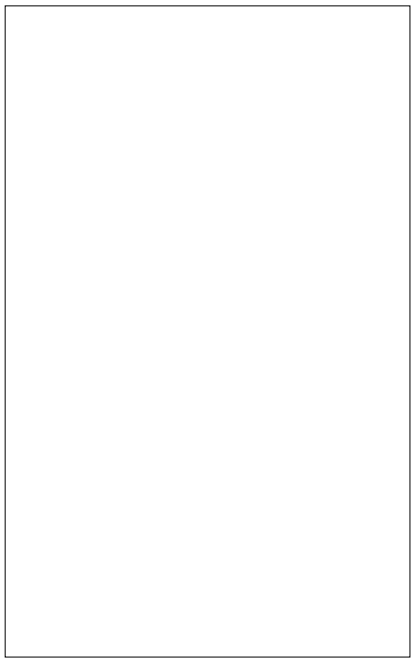
JCT855SJ 55A SCR

Rev.A.2.1

With high ability to withstand the shock loading of large current, JCT855SJ SCR provides high dV/dt rate with strong resistance to electromagnetic interference.It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-247J is RoHS compliant.



Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operat(er)7 (e)10unctit7Tm [(O)2 (per)7u(nt)2 (ur2.3 (a (a)10 (ng)10 (e)]TJ 0 TTc 0 Tw 1.94 0 T			

Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	- - -	10	50	mA

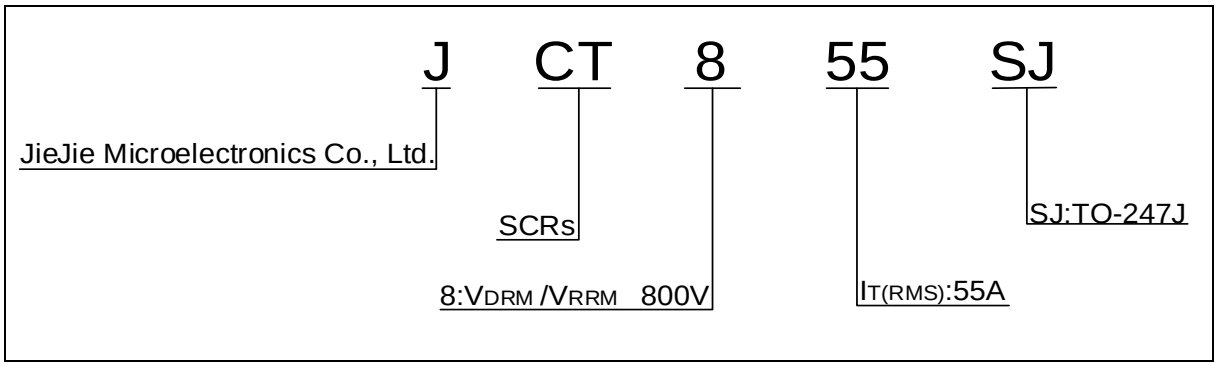

J
CT
8
55
SJ
JieJie Microelectronics Co., Ltd.
SCRs
8:VDRM /VRRM 800V
IT(RMS):55A
SJ:TO-247J

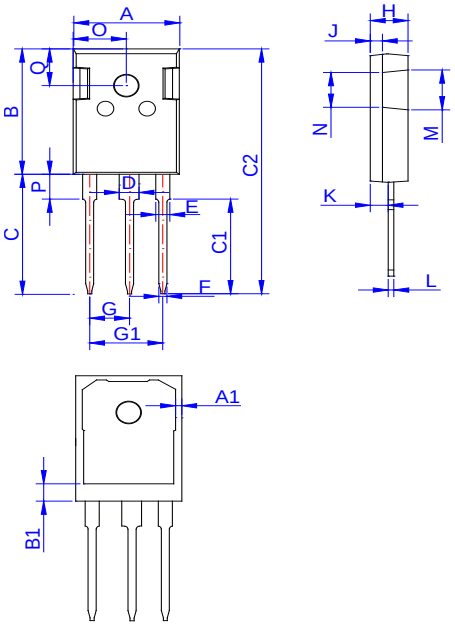
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT855SJ	800	10-50	TO-247J	30	Tube

Document Revision History

Date	Revision	Changes



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50		16.10	0.610		0.634
A1	1.15		1.55	0.045		0.061
B	20.80		21.20	0.819		0.835
B1	3.10		3.50	0.122		0.138
C	19.70		20.30	0.776		0.799
C1	15.50		16.10	0.610		0.634
C2	40.60		41.40	1.598		1.630
D	2.90		3.30	0.114		0.130
E	1.90		2.30	0.075		0.091
F	1.00		1.40	0.039		0.055
G		5.44			0.214	
G1	10.68		11.08	0.420		0.436
H	4.80		5.20	0.189		0.205
J	1.90		2.10	0.075		0.083
K	2.20		2.50	0.087		0.098
L	0.41		0.79	0.016		0.031
M	3.70		3.90	0.146		0.154
N	3.55		3.70	0.140		0.146
O	7.60		8.20	0.299		0.323
P	4.05		4.25	0.159		0.167
Q	5.85		6.45	0.230		0.254

